

## Silicon PNP Power Transistors

## 2SA483

## DESCRIPTION

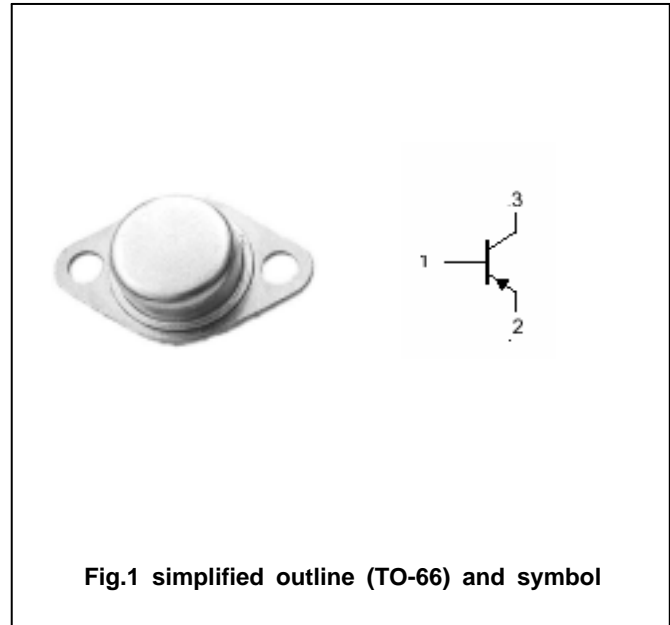
- With TO-66 package
- Complement to type 2SC783
- High voltage:  $V_{CEO} = -150V(\text{min})$

## APPLICATIONS

- Power amplifier applications
- Vertical output applications

## PINNING(see Fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Emitter     |
| 3   | Collector   |

Absolute maximum ratings( $T_a = \quad$ )

| SYMBOL    | PARAMETER                   | CONDITIONS     | VALUE   | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter   | -150    | V    |
| $V_{CEO}$ | Collector-emitter voltage   | Open base      | -150    | V    |
| $V_{EBO}$ | Emitter-base voltage        | Open collector | -5      | V    |
| $I_C$     | Collector current           |                | -1.5    | A    |
| $I_E$     | Emitter current             |                | 1.5     | A    |
| $P_C$     | Collector power dissipation | $T_C = 25$     | 20      | W    |
| $T_j$     | Junction temperature        |                | 150     |      |
| $T_{stg}$ | Storage temperature         |                | -65~150 |      |

## Silicon PNP Power Transistors

## 2SA483

## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS   | MIN  | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =-10mA ; I <sub>B</sub> =0            | -150 |      |      | V    |
| V <sub>(BR)CBO</sub> | Collector-base breakdown voltage     | I <sub>C</sub> =-0.5mA ; I <sub>E</sub> =0           | -150 |      |      | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =-0.5A ; I <sub>B</sub> =-50mA        |      |      | -1.8 | V    |
| V <sub>BE</sub>      | Base-emitter on voltage              | I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-10V        |      |      | -1.8 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =-150V ; I <sub>E</sub> =0           |      |      | -0.1 | mA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-5V ; I <sub>C</sub> =0             |      |      | -0.1 | mA   |
| h <sub>FE</sub>      | DC current gain                      | I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-10V        | 30   |      | 240  |      |
| C <sub>OB</sub>      | Output capacitance                   | I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1.0MHz |      | 50   |      | pF   |
| f <sub>T</sub>       | Transition frequency                 | I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-10V        |      | 10   |      | MHz  |

◆ h<sub>FE</sub> Classifications

| R     | O      | Y       |
|-------|--------|---------|
| 30-80 | 70-140 | 120-240 |

Silicon PNP Power Transistors

2SA483

PACKAGE OUTLINE

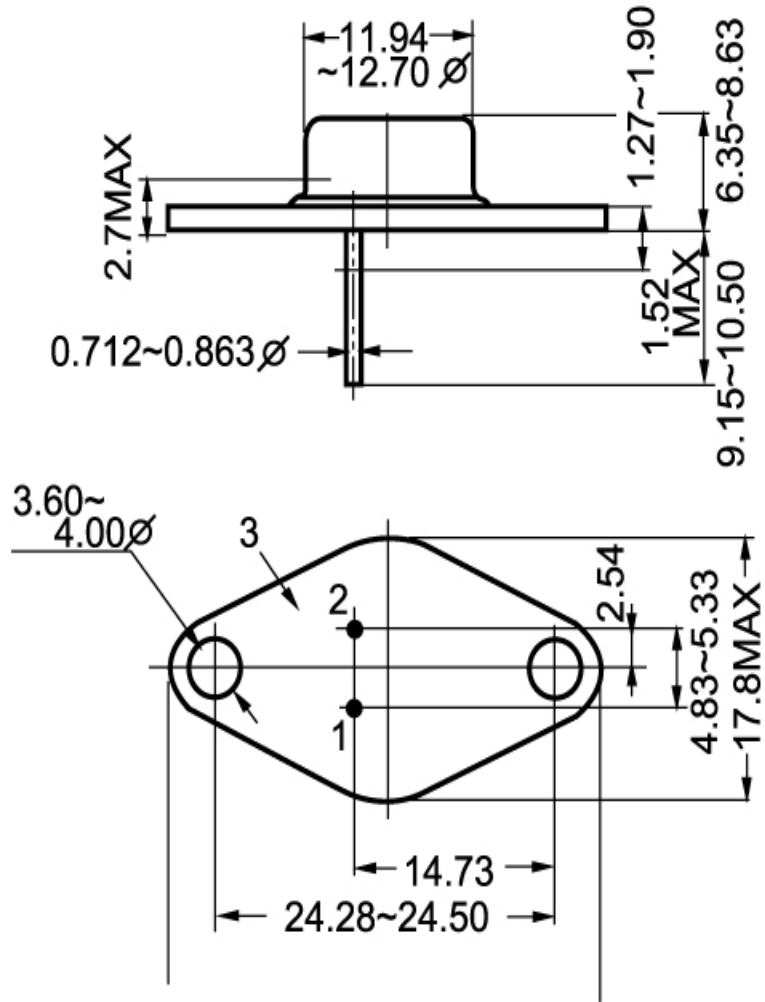


Fig.2 outline dimensions